ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089
http://www.nteinc.com

NTE2328 (NPN) & NTE2329 (PNP)
Silicon Complementary Transistors
Audio Power Output
TO3PBL Type Package

Features:

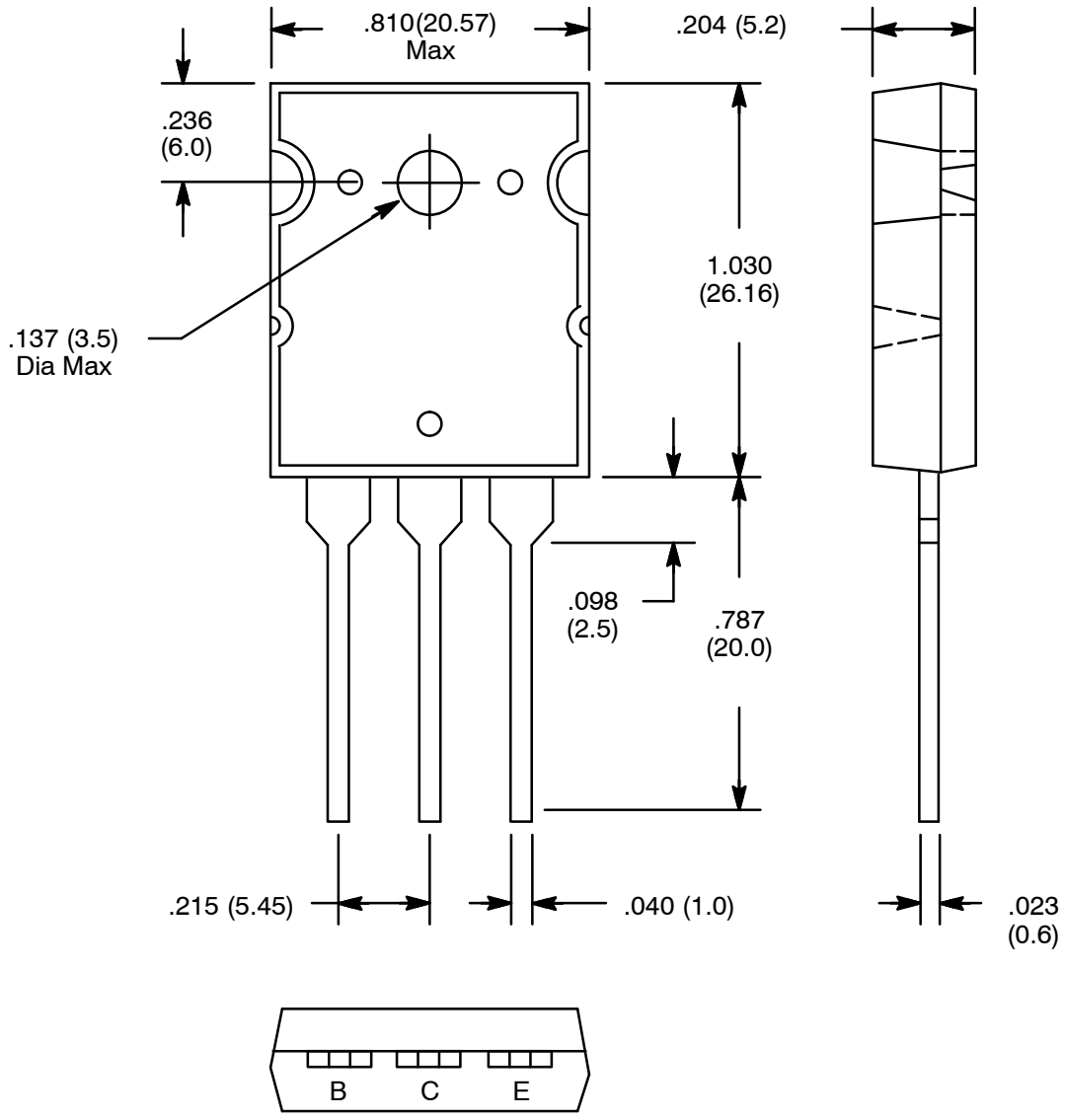
- Recommended for 100W High Fidelity Audio Frequency Amplifier Output Stage

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 200V
Collector–Emitter Voltage, V_{CEO} 200V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C 15A
Base Current, I_B 1.5A
Collector Power Dissipation (T_C = +25°C), P_C 150W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 200V, I_E = 0	–	–	5.0	A
Emitter Cutoff Current	I_{EBO}	V_{BE} = 5V, I_C = 0	–	–	5.0	A
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 50mA, I_B = 0	200	–	–	V
DC Current Gain	h_{FE1}	V_{CE} = 5V, I_C = 1A	55	–	160	
	h_{FE2}	V_{CE} = 5V, I_C = 8A	35	60	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 10A, I_B = 1A	–	1.5	3.0	V
Base–Emitter Voltage	V_{BE}	V_{CE} = 5V, I_C = 8A	–	1.0	1.5	V
Transistion Frequency	f_T	V_{CE} = 5V, I_C = 1A	–	25	–	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	–	470	–	pF



Note: Collector connected to heat sink.